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2004 05 27

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(22) 2002 11 20

(71) 136 - 1

(72) 237

103 1204

332 307

6 604 802

(74)

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(54)

(cross talk)

가

2e

1a 1e

2a 2e 1a 1e

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5 : 10 :

15 : 20 :

25 : 1 30 : 2

35 : 3 40 :

45 : / 55a, 55b, 55c :

60 : 65, 65a, 65b, 65c :

70 :

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가 , 1 3 2 3 1 2
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 (cross-talk)

가 , 가 가

(57)

1.

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 2 , 3 ; 1,
 1, 2, 3

2.

1 , 2 3 가

3.

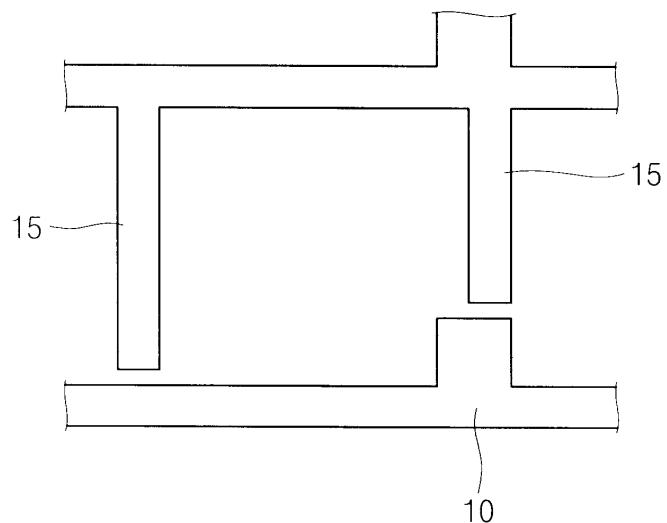
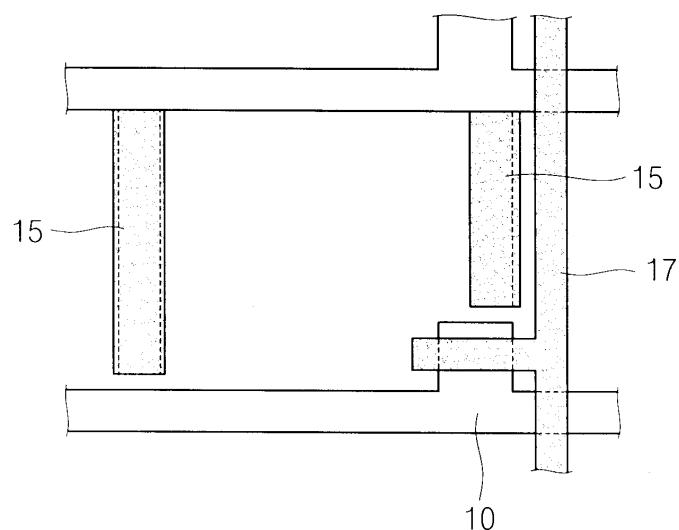
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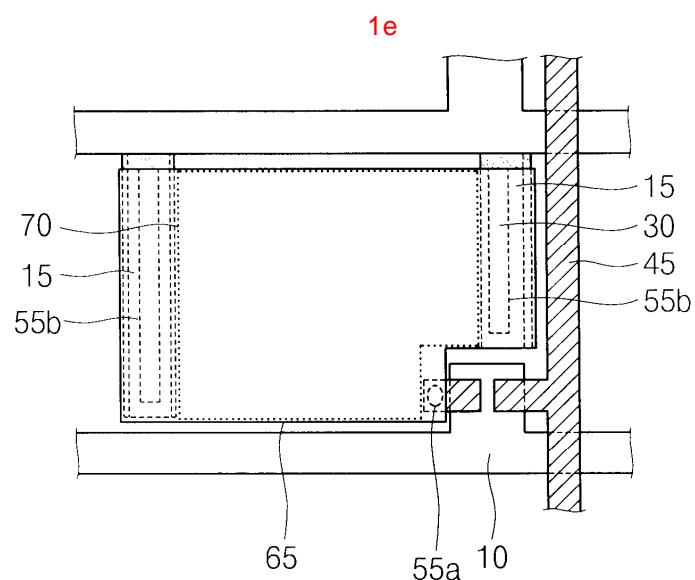
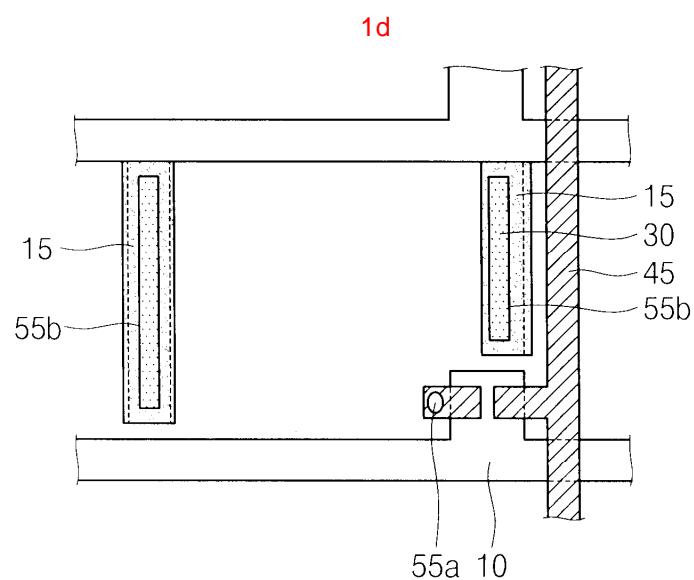
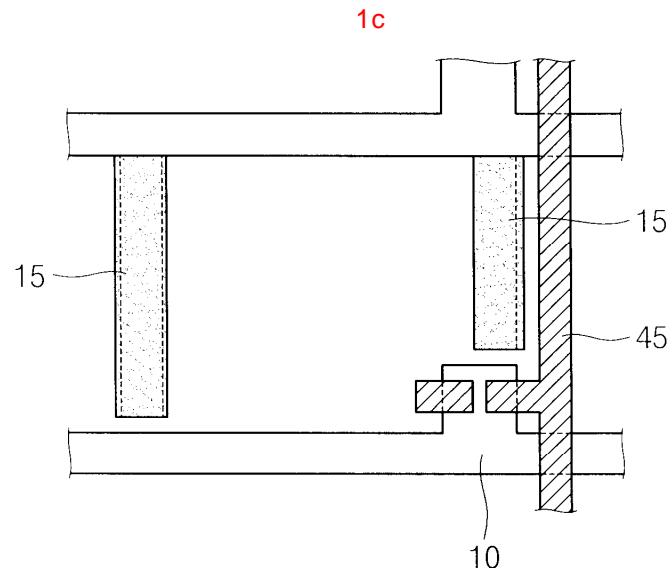
4.

1 , 1 2

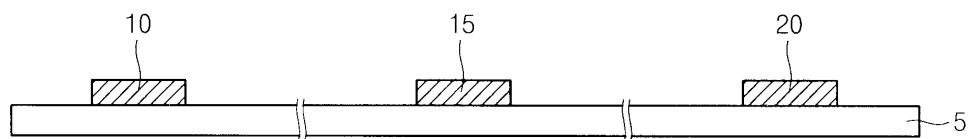
5.

1 , 3 500 10,000

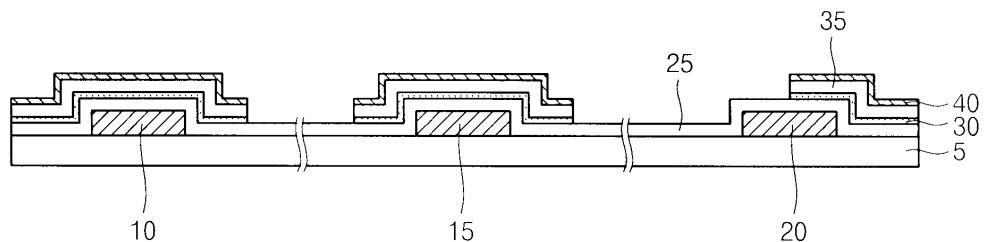
6.1 , 1 3 SiNx, SiC Al₂O₃**7.**1 , 2 SiON SiO₂**1a****1b**



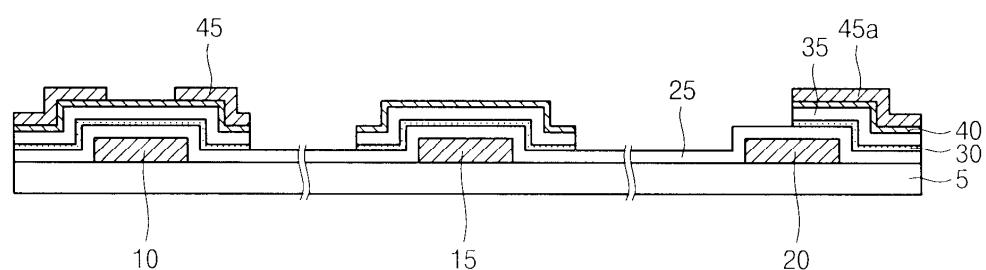
2a



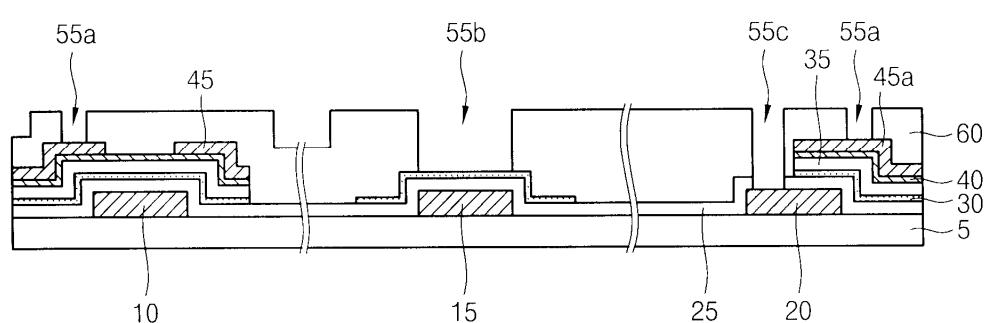
2b



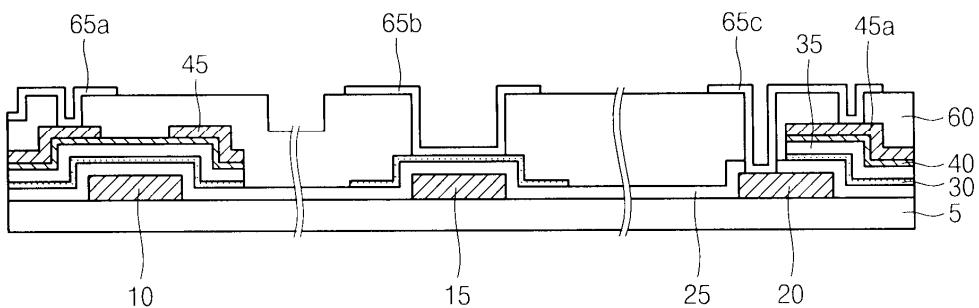
2c



2d



2e



专利名称(译)	液晶显示装置的制造方法		
公开(公告)号	KR1020040043892A	公开(公告)日	2004-05-27
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外部链接	Espacenet		

摘要(译)

根据本发明，保护膜形成在形成非晶层的非晶层上的源极和漏极的步骤的上部：栅极电极上部：结果。并且这选择性地被图案化并且它包括源电极，相应的第一和第二暴露第二绝缘层在存储电极和焊盘电极上，以及形成3个通孔的步骤和在保护电极上形成透明电极的步骤电影包括第一和第二，以及3个通孔。

